

A [your delay] FO4_(1V), [your energy] E_{u(1V)} 4-bit Absolute-Value Detector

Names

Definitions:

Unit delay = $FO4_{(1V)}$ -- inverter delay at Vdd = 1V Unit energy = $E_{u(1V)}$ -- energy associated with 1x inverter Cgate at Vdd = 1V If you scale Vdd, include the effect on delay and energy

Design Summary

Week 5 Week 7

- 1a) Circuit topology, 1b) Circuit Style
 - (e.g. Ripple –carry Adder + Comparator, static CMOS)
 - 1c) justify your selection of (A) and (b)
 (e.g. moderate Area, fast, regular design)
- Sizing + Vdd optimization / Sizing impact [see slide 13]:
 - Delay increase: [] % (out of 50%) | Energy reduction: [] %
- Sizing + Vdd optimization / V_{DD} impact [see slide 13]:
 - Delay increase: [] % (out of 50%) | Energy reduction: [] %

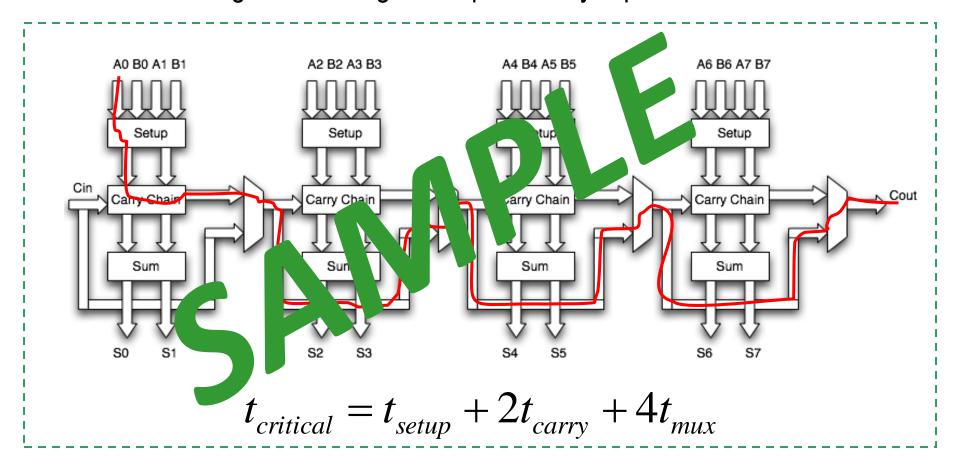
V _{DD}	Critical path delay	Total energy
1 V	$t_{p_IN \rightarrow OUT} = [] FO4_{(1V)}$	$E = [] E_{u(1V)}$
[] V	t _{p_IN→OUT} = [] FO4 _(1V)	$E = [] E_{u(1V)}$

Identify which IN and OUT pin gives worst-case delay

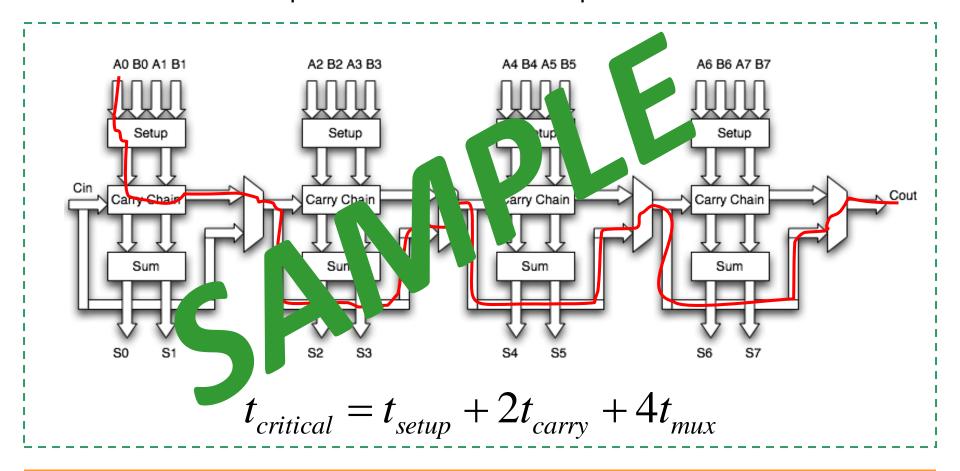
- Provide schematic of your circuit
- Give detailed reasoning about selection of your circuit topology and circuit style
 - What is unique about your selection of topology and style
 - What other options did you consider and why you discarded them
 - Etc.

Week 7

- Highlight critical path (w/ input and output bit position)
 - block diagram of design / crit-path delay equation



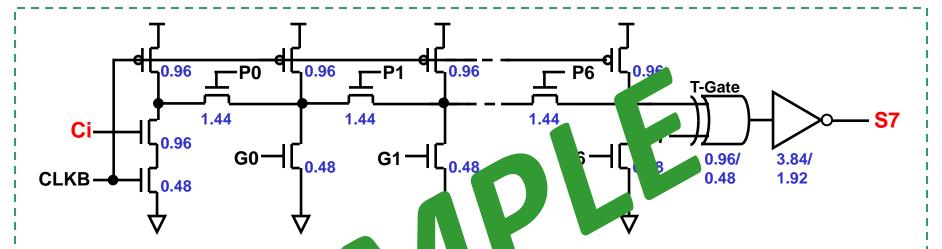
- Formulas that you used to model critical-path delay
 - Write down equation for the full critical path



- How did you decide about relative contribution of sizing and V_{DD} in your overall delay increase?
 - Explain your decision making process
 - Persuade that your selection is the best available

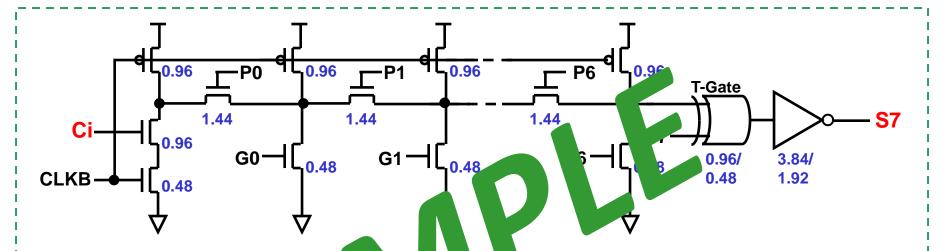
Move on to sizing and V_{DD} optimizations in subsequent slides

- Show sizing optimization of the critical path
 - Indicate sizing on the schematic



- Propagate Carry instead of Ca luc transistor count along Manchester chain
- NMOS only page gate is a Car noues are pre-charged to V_{DD} at CLK=0
- rer and G0:7 AND gates → footless Domino in Manchester chain
- Generate CO and not incorporate the 4X buffer in signal chain.

Discuss sizing of non-critical paths to minimize energy (add slides as necessary)



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- Show your derivation for V_{DD}^{opt}
- Calculate energy at V_{DD}^{opt}

Any Alternatives You Would Like to Discuss?

Week 7

 If you made significant effort in some alternative design, provide 1-slide summary of your findings

Discussion

Week 7

Three most important features of your design

- (e.g. Minimum delay through transistors sizing)
- (e.g. Logic optimization strategy for reduced area)

Given another chance, 3 things you would do different

- (e.g. Change topology, because...)
- (e.g. Optimize only last few stages to save design time)
- (e.g. Nothing, I nailed it down! ;))

11-12 slides + discussion
Each team member to present 3-4 slides

Project Guidance / What to Turn In?

Extended Project Abstract: 1 full page

- 80% to 100% of full page, 12-pt font, 1.2-line spacing
- One submission per group
- Include your project title and your names
- Document key design techniques, results, and findings

Individual Course Reflection: 1 full page

- Also 80% to 100% of full page, 12-pt font, 1.2-line spacing
- Individual submission for each student
- Reflect on key learning points from the workshop

Presentation Slides: each team member has to present

- See slides 1-11 of this guide
- One submission per group

Optimization of Sizing and Vdd Clarified

- Aim to optimize <u>Sizing and Vdd</u> jointly
 - Sizing only or Vdd only is suboptimal
- Useful software tools
 - MATLAB: fmincon function; Excel: Solver Add-on

